

AMENDMENTS TO THE SPECIFICATION

Please replace the first full paragraph on page 12 with the following amended paragraph:

IDC-a1,AMD

In the laser element produced as above, the curvature of the nitride-based semiconductor laser bar 13 is corrected so that light-emission points 12 in the nitride-based semiconductor laser bar 13 are aligned along a straight line approximately in correspondence with the shape of the surface 11a of the heat sink, as illustrated in FIG. 1B. In this example, the aforementioned light-emission-point displacement is 0.2 micrometers.

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last paragraph beginning on page 12
~~Please replace the first full paragraph on page 13 with the following amended paragraph:~~

IDC-a2,AMD

As mentioned before and illustrated in FIG. 2, the light-emission-point displacement is defined as a difference ($d_2 - d_1$) between the maximum d_2 and the minimum d_1 of the distances from the fixation surface of the heat sink to the centers of the light-emission points 12 in a plane perpendicular to the optical axis of lenses.

Please replace the first full paragraph on page 18 with the following amended

paragraph:

IDC-a3,AMD,M

The oscillation wavelength of the nitride-based semiconductor laser bar 13 produced as above ranges from 400 to 420 nm, and the output power is 30 mW. In the nitride-based semiconductor laser bar 13, twenty light-emission points 12 each having a width of about 2 micrometers are arranged with a pitch of about 500 micrometers over the length of about 1 cm.

IDC-a3,AMD,M

In addition, the nitride-based semiconductor laser bar 13 is convexedly curved on the p-electrode side. The light-emission-point displacement in the nitride-based semiconductor laser bar 13 before fixation to the heat sink 11 is about 10 micrometers.

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last paragraph beginning page 18

~~Please replace the first full paragraph on page 19 with the following amended paragraph:~~

IDC-a4,AMD

The above laser element according to the first embodiment of the present invention and a conventional laser element (prepared for comparison) are compared with respect to the light-emission-point displacement after each of the bonding to the heat sink and the cyclic heat treatment, where the nitride-based semiconductor laser bar used in the conventional laser element is produced in a similar manner to the nitride-based semiconductor laser bar 13 in the laser element according to the first embodiment so that the nitride-based semiconductor laser bar used in the conventional laser element has twenty light-emission points 12 which are arranged over the length of about 1 cm, and the light-emission-point displacement in the nitride-based semiconductor laser bar in the conventional laser element before fixation to a heat sink is also about 10 micrometers.